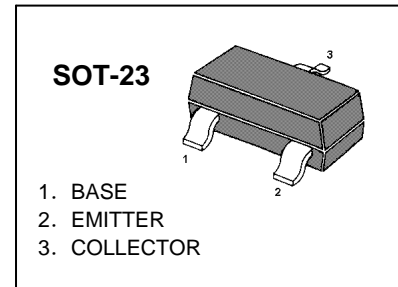


MMBT3906

TRANSISTOR (PNP)

FEATURES

- Complementary Type The NPN Transistor
- MMBT3904 is Recommended
- Epitaxial Planar Die Construction



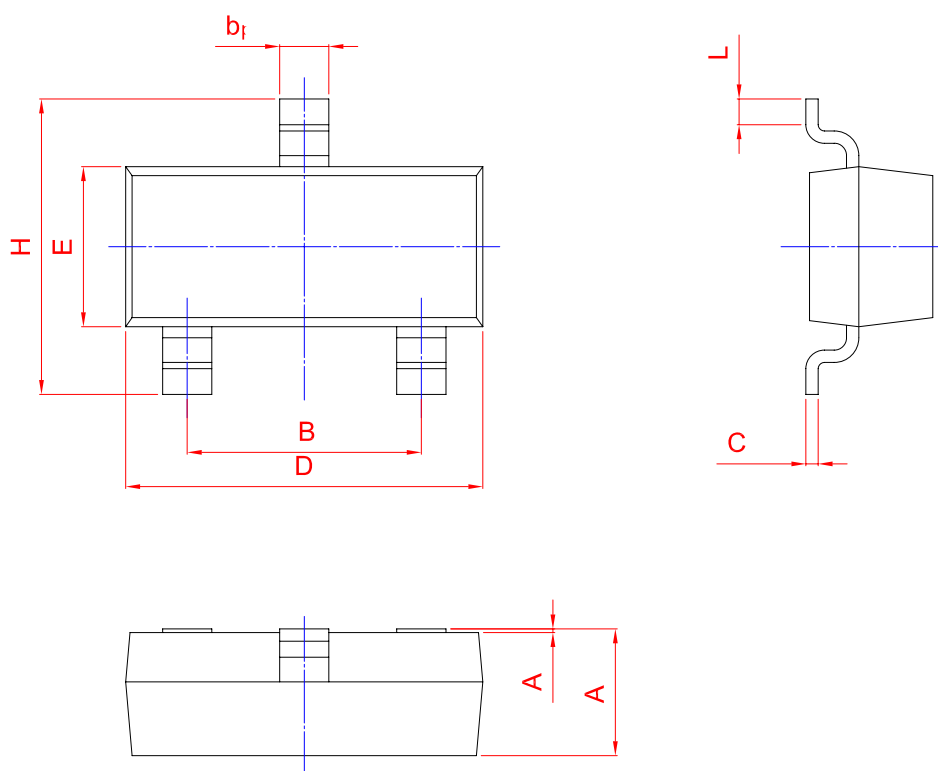
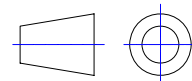
MARKING: 2A

MAXIMUM RATINGS ($T_a=25$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-200	mA
P_C	Total Device Dissipation	200	mW
R_{JA}	Thermal Resistance Junction to Ambient	625	/W
T_J	Junction Temperature	150	
T_{stg}	Storage Temperature	-55 ~ +150	

ELECTRICAL CHARACTERISTICS ($T_a=25$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-40V, I_E=0$		-0.1	μA
Collector cut-off current	I_{CEX}	$V_{CE}=-30V, V_{BE(off)}=-3V$		-50	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-10mA$	100	300	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-50mA$	60		
	$h_{FE(3)}$	$V_{CE}=-1V, I_C=-100mA$	30		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-50mA, I_B=-5mA$		-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-50mA, I_B=-5mA$		-0.95	V
Transition frequency	f_T	$V_{CE}=-20V, I_C=-10mA, f=100MHz$	300		MHz
Delay Time	t_d	$V_{CC}=-3V, V_{BE}=-0.5V$		35	nS
Rise Time	t_r	$I_C=-10mA, I_{B1}=-I_{B2}=-1mA$		35	nS
Storage Time	t_s	$V_{CC}=-3V, I_C=-10mA,$		225	nS
Fall Time	t_f	$I_{B1}=-I_{B2}=-1mA$		75	nS



UNIT	A		b_p	C	D	E	H_E	A_1	L_p
mm	1.40		0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95		0.35	0.08	2.70	1.20	2.20	0.013	0.20